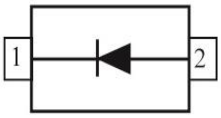
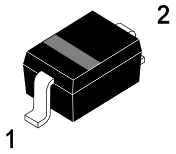
1N914W S High –Speed Switching Diode



1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.

Marking: 5D



SOD323

2. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Reverse Voltage	VR	100	V
Forward Current	IF	200	mA
Peak Forward Surge Current	IFMS	500	mA

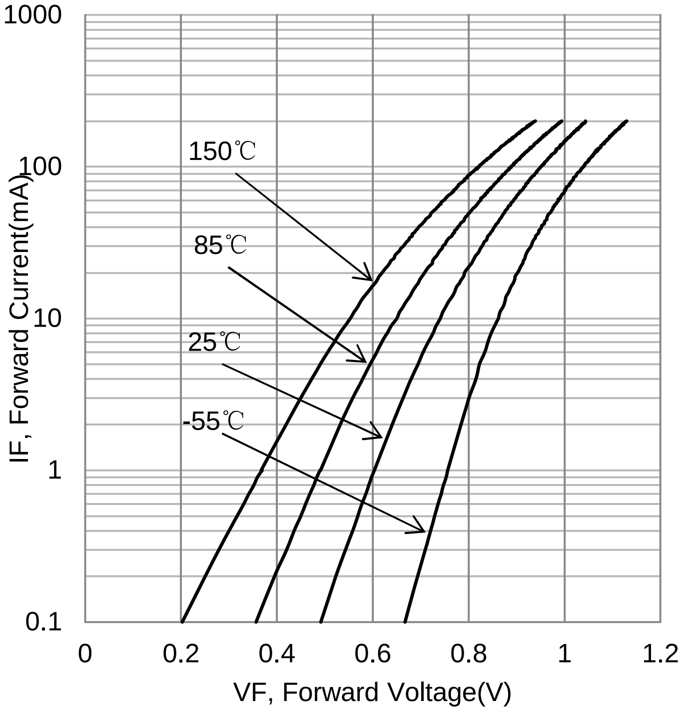
3. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR−4 Board (Note 1) @ TA = 25°C Derate above 25°C	PD	200 1.57	mW mW/°C
Thermal Resistance, Junction–to–Ambient(Note 1)	RΘJA	635	°C/W
Thermal Resistance, Junction–to–Case	RΘJC	350	°C/W
Junction and Storage temperature	TJ,Tstg	−55~+150	°C

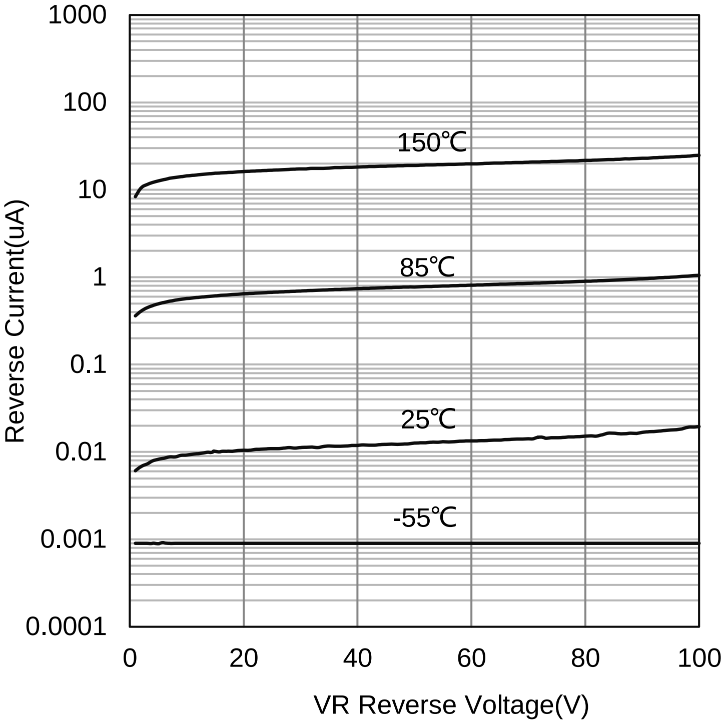
4. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage (IR = 100μA)	VBR	100	-	-	V
Reverse Voltage Leakage Current (VR = 20V) (VR = 75V)	IR	- -	- -	25 5	nA μA
Diode Capacitance (VR = 0, f = 1.0 MHz)	CT	-	-	4	pF
Forward Voltage (IF = 10 mA) (IF = 50 mA)	VF	- -	- -	1 1	V
Reverse Recovery Time (IF = IR = 10 mA)	trr	-	-	4	ns
Non-Repetitive Peak Forward Current (suqare wave;Tj=25 °Cprior to surge t=1 μs) (t=1ms) (t=1s)	IFSM	- -	- -	4 1	A

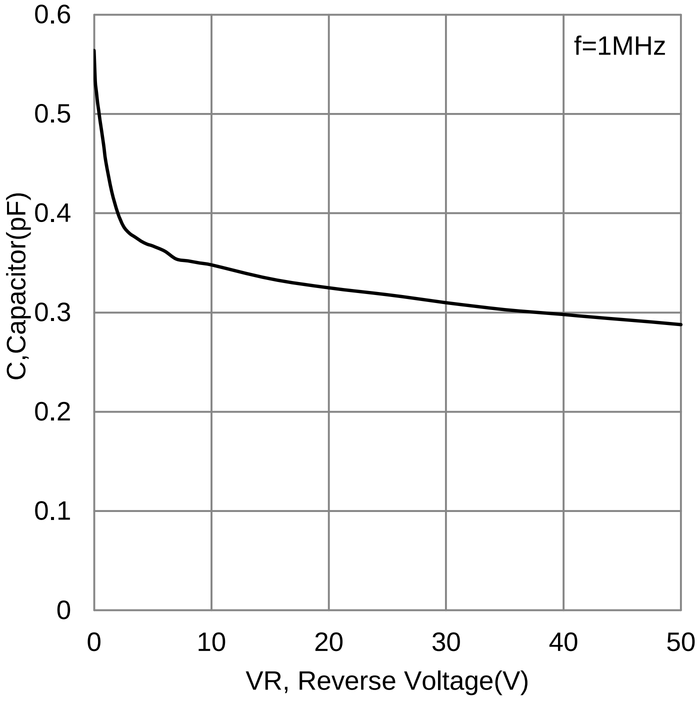
5. ELECTRICAL CHARACTERISTICS CURVES



Forward Characteristics



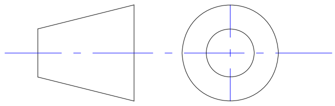
Reverse Characteristics

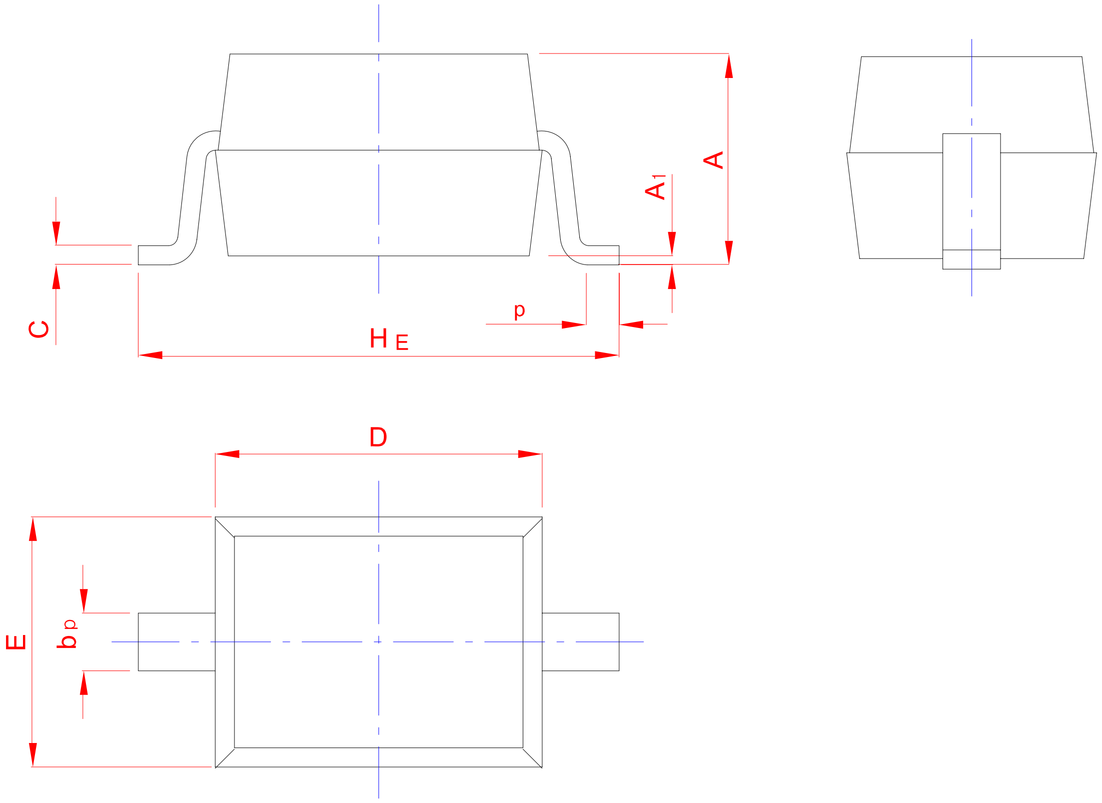


Capacitor Characteristics

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-323**





UNIT	A	b_p	C	D	E	H_E	A_1	L_p
mm	1.00 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30	0.10 0.01	0.50 0.20